
2SB649, 2SB649A

Silicon PNP Epitaxial

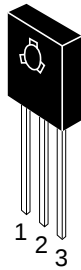
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Application

Low frequency power amplifier complementary pair with 2SD669/A

Outline

TO-126 MOD



- 1. Emitter
- 2. Collector
- 3. Base

2SB649, 2SB649A

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB649	2SB649A	
Collector to base voltage	V _{CBO}	−180	−180	V
Collector to emitter voltage	V _{CEO}	−120	−160	V
Emitter to base voltage	V _{EBO}	−5	−5	V
Collector current	I _C	−1.5	−1.5	A
Collector peak current	I _{C(peak)}	−3	−3	A
Collector power dissipation	P _C	1	1	W
	P _C ^{*1}	20	20	W
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	−55 to +150	−55 to +150	°C

Note: 1. Value at T_C = 25°C

Electrical Characteristics (Ta = 25°C)

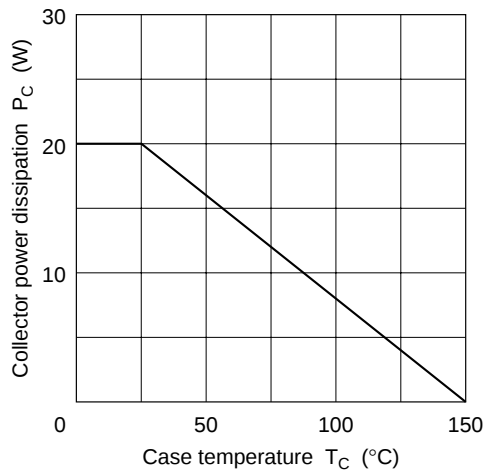
Item	Symbol	2SB649			2SB649A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-180	—	—	-180	—	—	V	$I_C = -1 \text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	—	—	-160	—	—	V	$I_C = -10 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -1 \text{ mA}, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-10	—	—	-10	μA	$V_{CB} = -160 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	200		$V_{CE} = -5 \text{ V}, I_C = -150 \text{ mA}$
	h_{FE2}	30	—	—	30	—	—		$V_{CE} = -5 \text{ V}, I_C = -500 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$
Base to emitter voltage	V_{BE}	—	—	-1.5	—	—	-1.5	V	$V_{CE} = -5 \text{ V}, I_C = -150 \text{ mA}$
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	$V_{CE} = -5 \text{ V}, I_C = -150 \text{ mA}$
Collector output capacitance	C_{ob}	—	27	—	—	27	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Notes: 1. The 2SB649 and 2SB649A are grouped by h_{FE1} as follows.

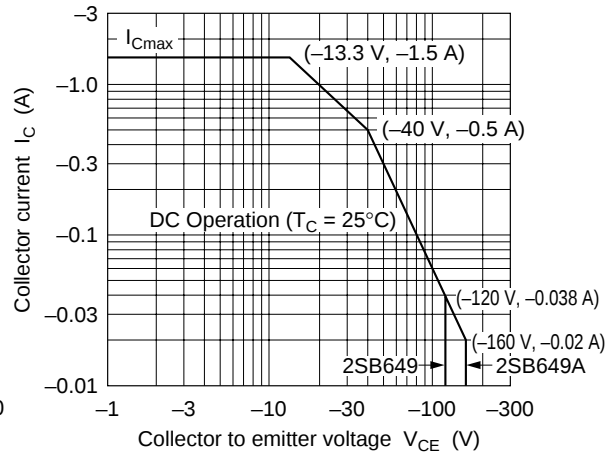
2. Pulse test

	B	C	D
2SB649	60 to 120	100 to 200	160 to 320
2SB649A	60 to 120	100 to 200	—

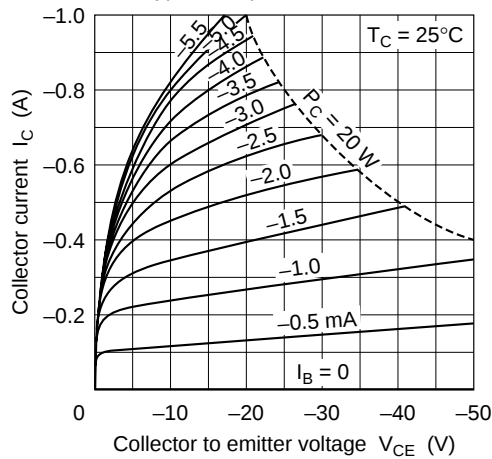
Maximum Collector Dissipation Curve



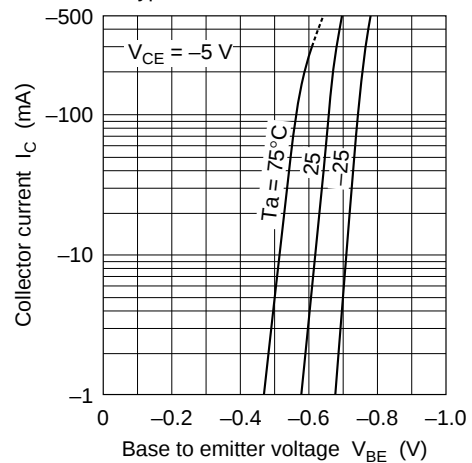
Area of Safe Operation



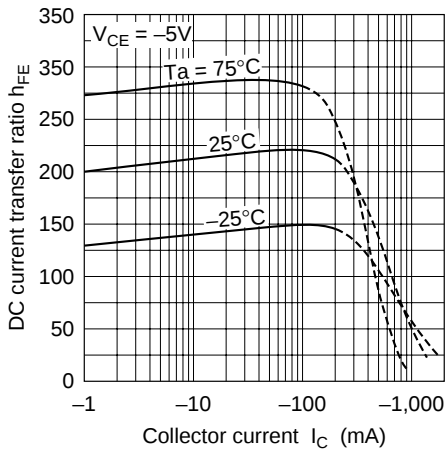
Typical Output Characteristics



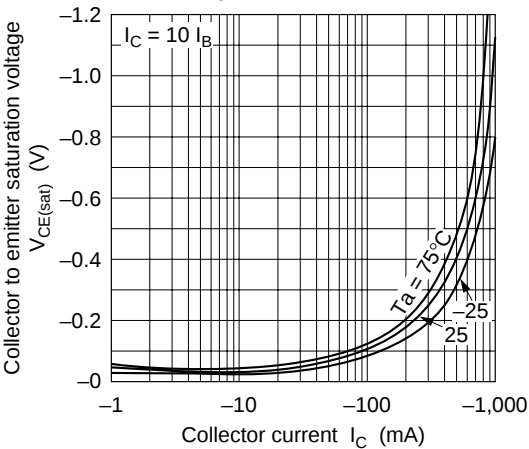
Typical Transfer Characteristics



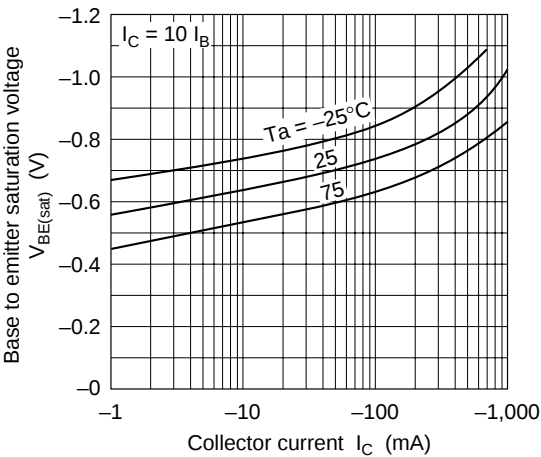
DC Current Transfer Ratio
vs. Collector Current



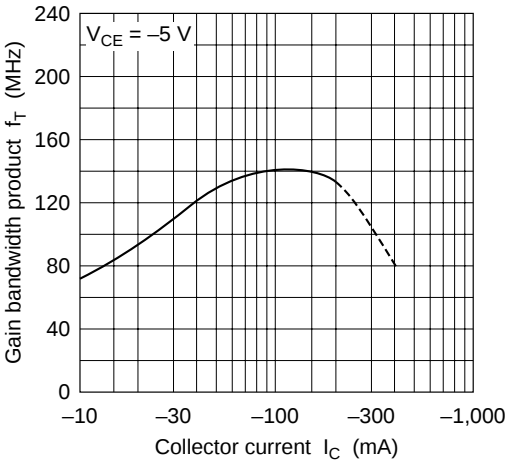
Collector to Emitter Saturation
Voltage vs. Collector Current

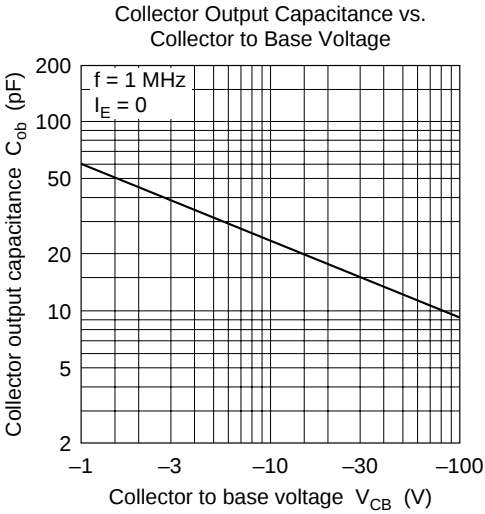


Base to Emitter Saturation Voltage
vs. Collector Current



Gain Bandwidth Product
vs. Collector Current





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